# ON Semiconductor

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ON Semiconductor®

# FDB045AN08A0-F085

## N-Channel PowerTrench® MOSFET

## 75V, 80A, 4.5mΩ

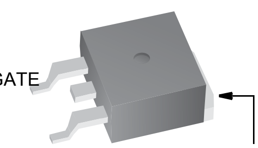
### Features

- $r_{DS(ON)}$ = 3.9mΩ (Typ.), $V_{GS}$ = 10V, $I_D$ = 80A
- $Q_g$(tot) = 92nC (Typ.), $V_{GS}$ = 10V
- Low Miller Charge
- Low $Q_{RR}$ Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant

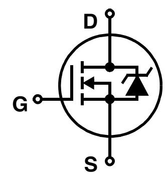
Formerly developmental type 82684

### Applications

- 42V Automotive Load Control
- Starter / Alternator Systems
- Electronic Power Steering Systems
- Electronic Valve Train Systems
- DC-DC converters and Off-line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V systems




**TO-263AB**
FDB SERIES




## MOSFET Maximum Ratings $T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|---|---|---|---|
| $V_{DSS}$ | Drain to Source Voltage | 75 | V |
| $V_{GS}$ | Gate to Source Voltage | ±20 | V |
| $I_D$ | Drain Current<br>Continuous ($T_C$ < 137°C, $V_{GS}$ = 10V) | 90 | A |
| | Continuous ($T_{amb}$ = 25°C, $V_{GS}$ = 10V, with $R_{\theta JA}$ = 43°C/W) | 19 | A |
| | Pulsed | Figure 4 | A |
| $E_{AS}$ | Single Pulse Avalanche Energy (Note 1) | 600 | mJ |
| $P_D$ | Power dissipation | 310 | W |
| | Derate above 25°C | 2.0 | W/°C |
| $T_J$, $T_{STG}$ | Operating and Storage Temperature | -55 to 175 | °C |

## Thermal Characteristics

| | | | |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case TO-263 | 0.48 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient TO-263 (Note 2) | 62 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient TO-263, 1in$^2$ copper pad area | 43 | °C/W |

**This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/**

**All ON Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.**

## Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|---|---|---|---|---|---|
| FDB045AN08A0 | FDB045AN08A0-F085 | TO-263AB | 330mm | 24mm | 800 units |

## Electrical Characteristics $T_C$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $B_{VDSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250μA, $V_{GS}$ = 0V | 75 | - | - | V |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 60V, $V_{GS}$ = 0V | - | - | 1 | μA |
| | | $V_{DS}$ = 60V, $V_{GS}$ = 0V, $T_C$ = 150°C | - | - | 250 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20V | - | - | ±100 | nA |
| **On Characteristics** | | | | | | |
| $V_{GS(TH)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}$, $I_D$ = 250μA | 2 | - | 4 | V |
| $r_{DS(ON)}$ | Drain to Source On Resistance | $I_D$ = 80A, $V_{GS}$ = 10V | - | 0.0039 | 0.0045 | Ω |
| | | $I_D$ = 37A, $V_{GS}$ = 6V | - | 0.0056 | 0.0084 | Ω |
| | | $I_D$ = 80A, $V_{GS}$ = 10V, $T_J$ = 175°C | - | 0.008 | 0.011 | Ω |
| **Dynamic Characteristics** | | | | | | |
| $C_{ISS}$ | Input Capacitance | $V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz | - | 6600 | - | pF |
| $C_{OSS}$ | Output Capacitance | | - | 1000 | - | pF |
| $C_{RSS}$ | Reverse Transfer Capacitance | | - | 240 | - | pF |
| $Q_{g(TOT)}$ | Total Gate Charge at 10V | $V_{GS}$ = 0V to 10V; $V_{DD}$ = 40V, $I_D$ = 80A, $I_g$ = 1.0mA | | 92 | 138 | nC |
| $Q_{g(TH)}$ | Threshold Gate Charge | $V_{GS}$ = 0V to 2V | - | 11 | 17 | nC |
| $Q_{gs}$ | Gate to Source Gate Charge | | - | 27 | - | nC |
| $Q_{gs2}$ | Gate Charge Threshold to Plateau | | - | 16 | - | nC |
| $Q_{gd}$ | Gate to Drain "Miller" Charge | | - | 21 | - | nC |
| **Switching Characteristics** ($V_{GS}$ = 10V) | | | | | | |
| $t_{ON}$ | Turn-On Time | $V_{DD}$ = 40V, $I_D$ = 80A, $V_{GS}$ = 10V, $R_{GS}$ = 3.3Ω | - | - | 160 | ns |
| $t_{d(ON)}$ | Turn-On Delay Time | | - | 18 | - | ns |
| $t_r$ | Rise Time | | - | 88 | - | ns |
| $t_{d(OFF)}$ | Turn-Off Delay Time | | - | 40 | - | ns |
| $t_f$ | Fall Time | | - | 45 | - | ns |
| $t_{OFF}$ | Turn-Off Time | | - | - | 128 | ns |
| **Drain-Source Diode Characteristics** | | | | | | |
| $V_{SD}$ | Source to Drain Diode Voltage | $I_{SD}$ = 80A | - | - | 1.25 | V |
| | | $I_{SD}$ = 40A | - | - | 1.0 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_{SD}$ = 75A, $dI_{SD}/dt$ = 100A/μs | - | - | 53 | ns |
| $Q_{RR}$ | Reverse Recovered Charge | $I_{SD}$ = 75A, $dI_{SD}/dt$ = 100A/μs | - | - | 54 | nC |

**Notes:**
**1:** Starting $T_J$ = 25°C, L = 0.48mH, $I_{AS}$ = 50A.
**2:** Pulse Width = 100s

## Typical Characteristics $T_C$ = 25°C unless otherwise noted

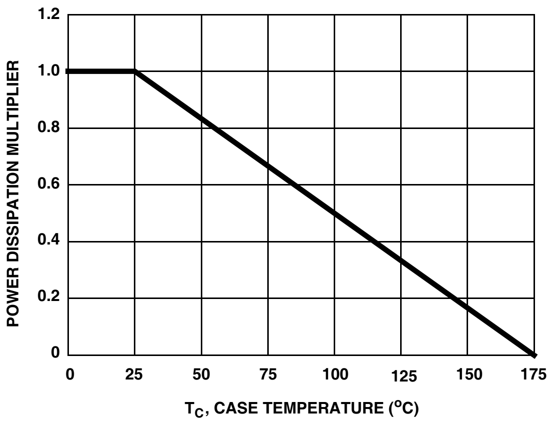



Figure 1. Normalized Power Dissipation vs Ambient Temperature

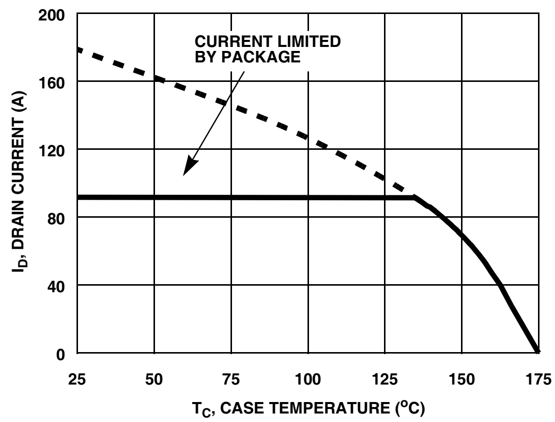



Figure 2. Maximum Continuous Drain Current vs Case Temperature

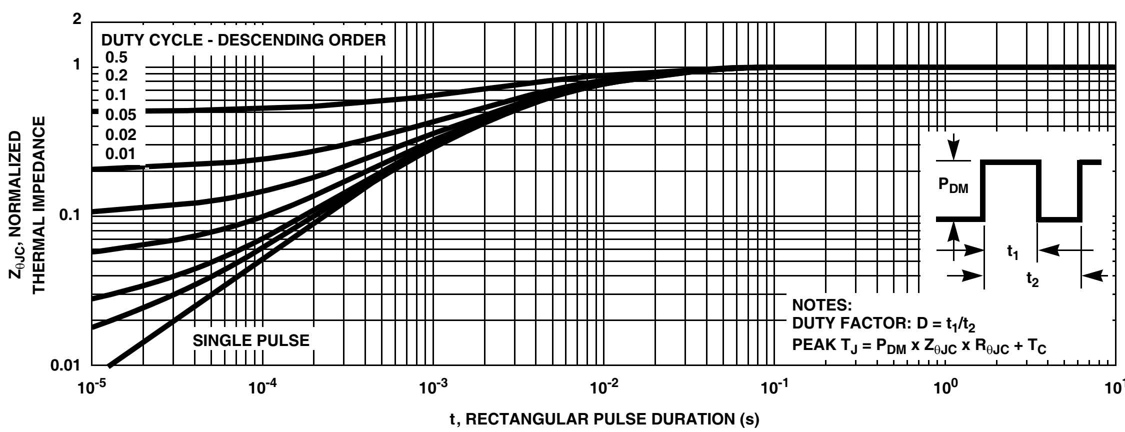



Figure 3. Normalized Maximum Transient Thermal Impedance

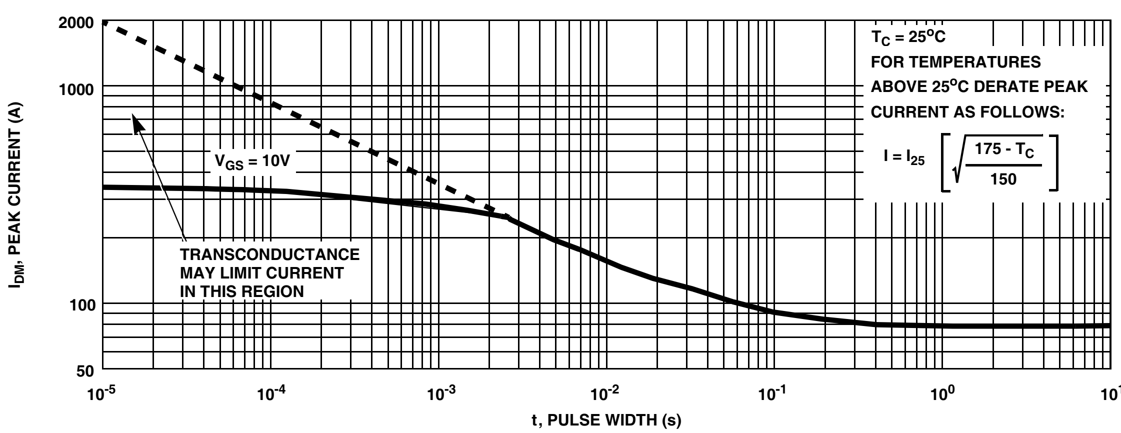



Figure 4. Peak Current Capability

## Typical Characteristics $T_C$ = 25°C unless otherwise noted

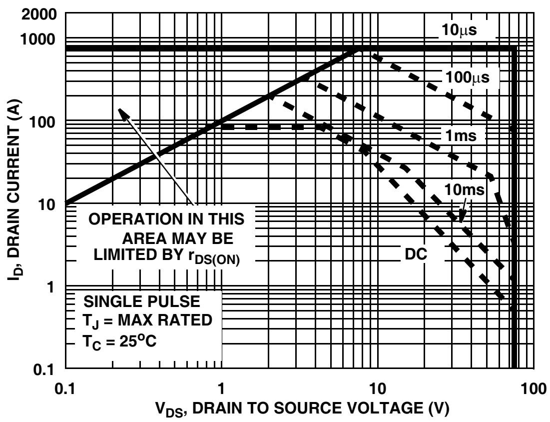
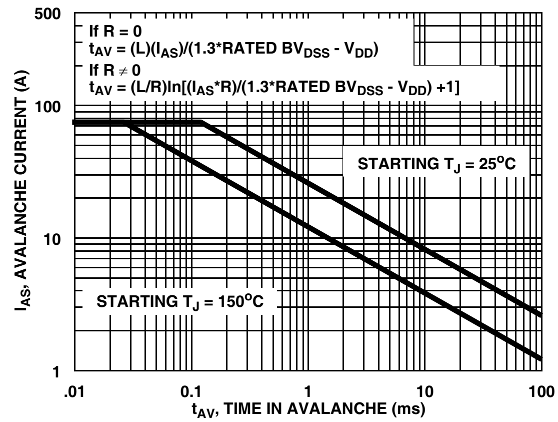



**Figure 5. Forward Bias Safe Operating Area**




NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

**Figure 6. Unclamped Inductive Switching Capability**

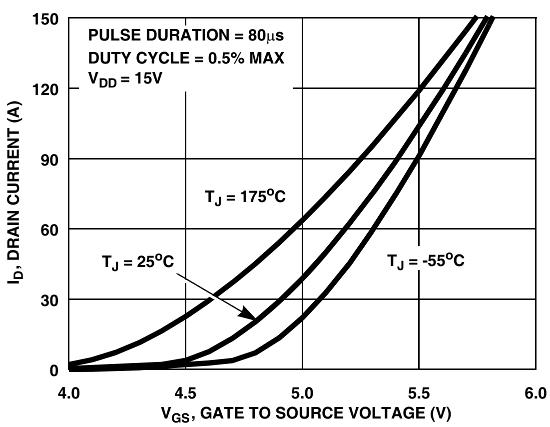



**Figure 7. Transfer Characteristics**

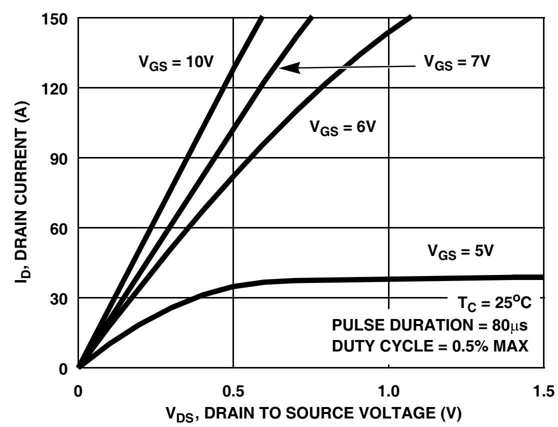



**Figure 8. Saturation Characteristics**

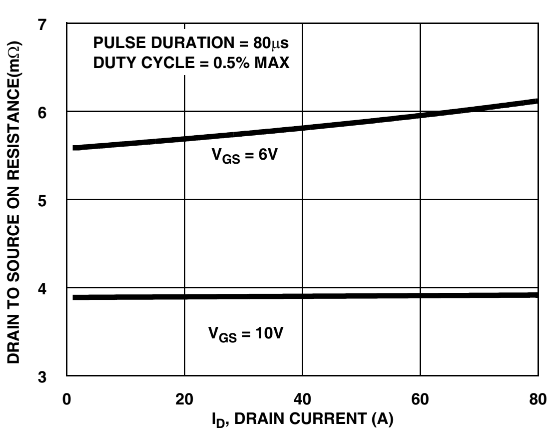



**Figure 9. Drain to Source On Resistance vs Drain Current**

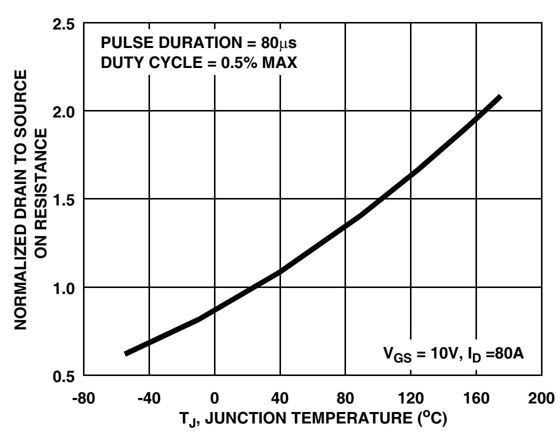



**Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature**

## Typical Characteristics $T_C$ = 25°C unless otherwise noted

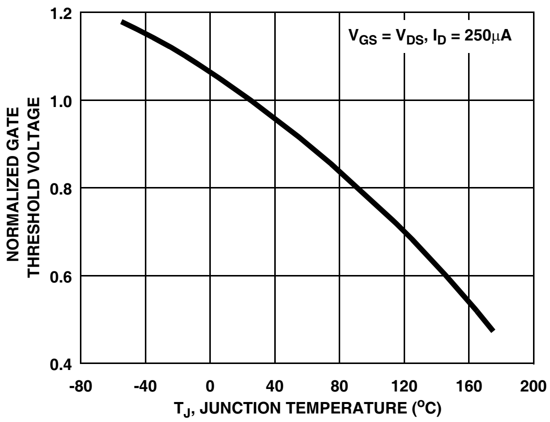



**Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature**

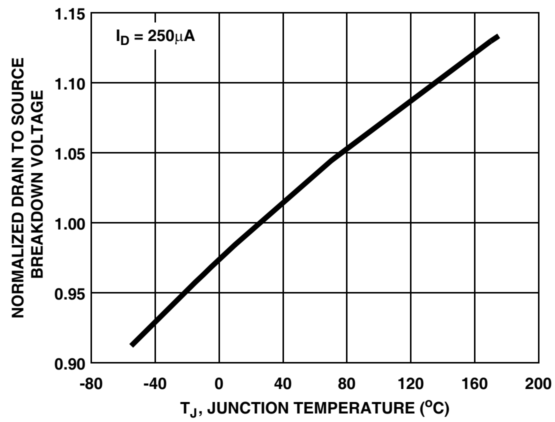



**Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature**

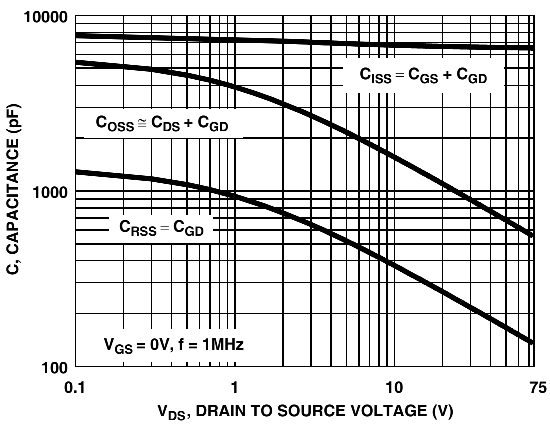



**Figure 13. Capacitance vs Drain to Source Voltage**

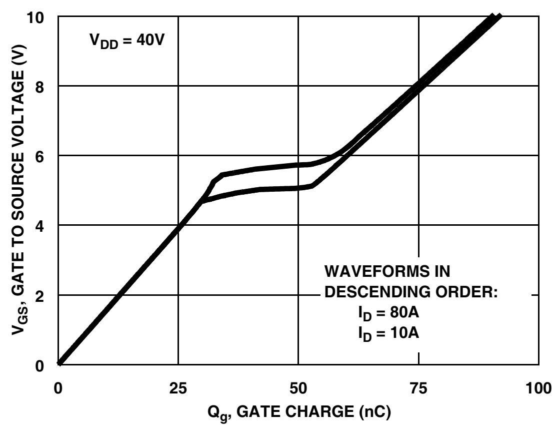



**Figure 14. Gate Charge Waveforms for Constant Gate Currents**

## Test Circuits and Waveforms

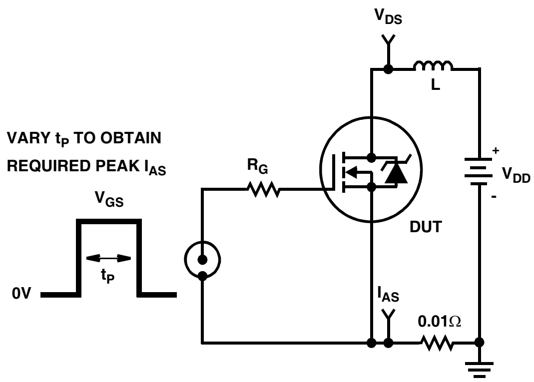



Figure 15. Unclamped Energy Test Circuit

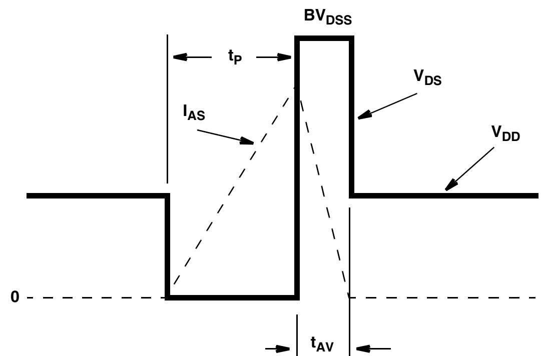



Figure 16. Unclamped Energy Waveforms

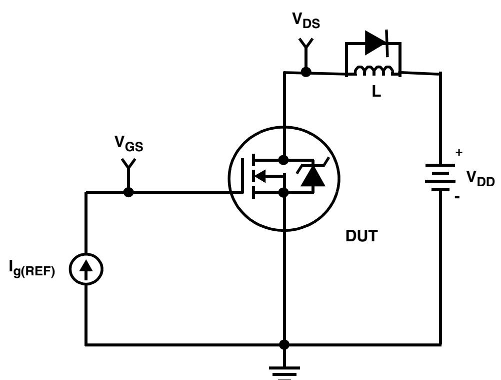



Figure 17. Gate Charge Test Circuit

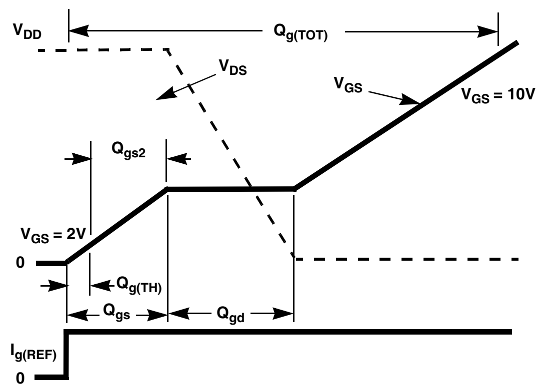



Figure 18. Gate Charge Waveforms

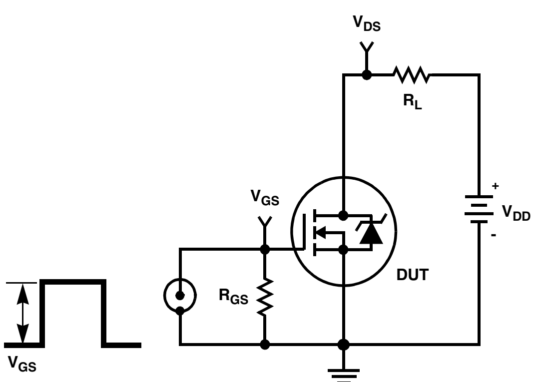



Figure 19. Switching Time Test Circuit

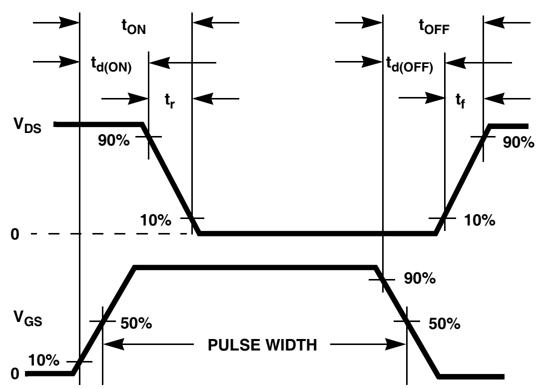



Figure 20. Switching Time Waveforms

## *Thermal Resistance vs. Mounting Pad Area*

The maximum rated junction temperature, $T_{JM}$, and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation, $P_{DM}$, in an application. Therefore the application's ambient temperature, $T_A$ ($^oC$), and thermal resistance $R_{\theta JA}$ ($^oC/W$) must be reviewed to ensure that $T_{JM}$ is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \qquad \text{(EQ. 1)}$$

In using surface mount devices such as the TO-263 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of $P_{DM}$ is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

ON Semiconductor provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the $R_{\theta JA}$ for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the ON Semiconductor device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2 or 3. Equation 2 is used for copper area defined in inches square and equation 3 is for area in centimeters square. The area, in square inches or square centimeters is the top copper area including the gate and source pads.

$$R_{\theta JA} = 26.51 + \frac{19.84}{(0.262 + Area)} \qquad \text{(EQ. 2)}$$

Area in Inches Squared

$$R_{\theta JA} = 26.51 + \frac{128}{(1.69 + Area)} \qquad \text{(EQ. 3)}$$

Area in Centimeter Squared

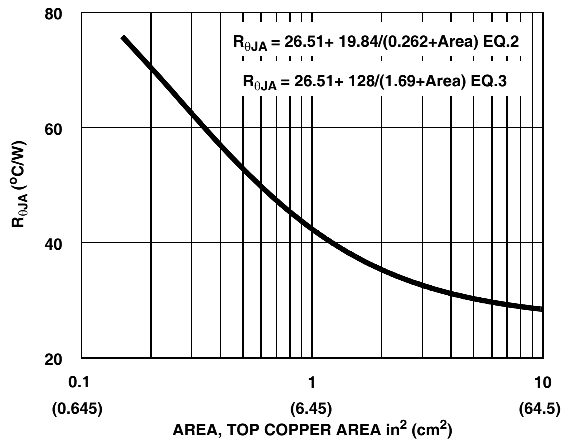
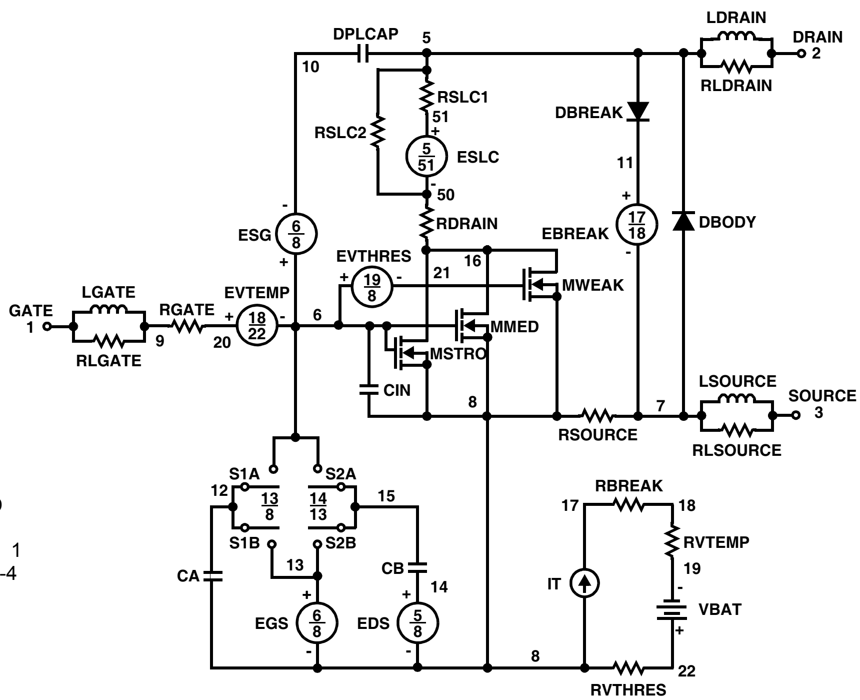



**Figure 21. Thermal Resistance vs Mounting Pad Area**

## PSPICE Electrical Model

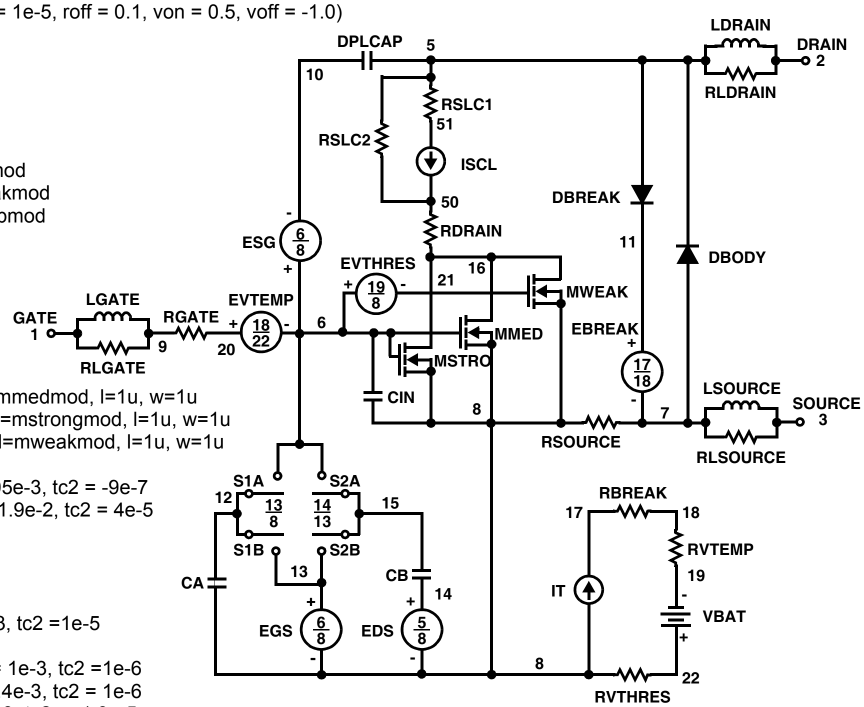



```
.SUBCKT FDB045AN08A0 2 1 3 ;        rev March 2002
CA  12  8 1.5e-9
CB  15  14 1.5e-9
CIN  6  8 6.4e-9

DBODY 7 5 DBODYMOD
DBREAK 5 11  DBREAKMOD
DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17  18 82.3
EDS  14  8  5  8 1
EGS  13  8  6  8 1
ESG 6 10 6 8 1
EVTHRES 6 21 19 8  1
EVTEMP 20 6 18 22 1

IT  8  17  1

LDRAIN 2 5 1e-9
LGATE 1  9 4.81e-9
LSOURCE  3  7 4.63e-9

MMED 16 6 8 8 MMEDMOD
MSTRO 16 6 8 8 MSTROMOD
MWEAK 16 21 8 8 MWEAKMOD

RBREAK  17  18  RBREAKMOD  1
RDRAIN 50 16 RDRAINMOD 9e-4
RGATE  9  20 1.36
RLDRAIN 2 5 10
RLGATE 1 9 48.1
RLSOURCE 3 7 46.3
RSLC1 5 51 RSLCMOD 1e-6
RSLC2 5 50 1e3
RSOURCE  8  7  RSOURCEMOD 2.3e-3
RVTHRES 22 8 RVTHRESMOD  1
RVTEMP 18 19 RVTEMPMOD 1

S1A  6  12  13  8  S1AMOD
S1B  13  12  13  8  S1BMOD
S2A  6  15  14  13  S2AMOD
S2B  13  15  14  13  S2BMOD

VBAT 22 19  DC  1

ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*250),10))}

.MODEL DBODYMOD D (IS = 2.4e-11 N = 1.04  RS = 1.76e-3  TRS1 = 2.7e-3  TRS2 = 2e-7 XTI=3.9  CJO = 4.35e-9  TT = 1e-8
M = 5.4e-1)
.MODEL DBREAKMOD D (RS = 1.5e-1  TRS1 = 1e-3  TRS2 = -8.9e-6)
.MODEL DPLCAPMOD D (CJO = 1.35e-9  IS = 1e-30  N = 10 M = 0.53)
.MODEL MMEDMOD NMOS (VTO = 3.7 KP = 9  IS =1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 1.36)
.MODEL MSTROMOD NMOS (VTO = 4.4 KP = 250  IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL MWEAKMOD NMOS (VTO = 3.05 KP = 0.03 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 1.36e1 RS = 0.1)
.MODEL RBREAKMOD RES (TC1 = 1.05e-3  TC2 = -9e-7)
.MODEL RDRAINMOD RES (TC1 = 1.9e-2  TC2 = 4e-5)
.MODEL RSLCMOD RES (TC1 = 1.3e-3 TC2 = 1e-5)
.MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 1e-6)
.MODEL RVTHRESMOD RES (TC1 = -6e-3 TC2 = -1.9e-5)
.MODEL RVTEMPMOD RES (TC1 = -2.4e-3  TC2 = 1e-6)

.MODEL S1AMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -4.0  VOFF= -1.5)
.MODEL S1BMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -1.5  VOFF= -4.0)
.MODEL S2AMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = -1.0  VOFF= 0.5)
.MODEL S2BMOD VSWITCH (RON = 1e-5  ROFF = 0.1  VON = 0.5  VOFF= -1.0)

.ENDS
```

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

## *SABER Electrical Model*

```
REV March 2002
template FDB045AN08A0 n2,n1,n3
electrical n2,n1,n3
{
var i iscl
dp..model dbodymod = (isl = 2.4e-11, n1 = 1.04, rs = 1.76e-3, trs1 = 2.7e-3, trs2 = 2e-7, xti = 3.9, cjo = 4.35e-9, tt = 1e-8, m = 5.4e-1)
dp..model dbreakmod = (rs = 1.5e-1, trs1 = 1e-3, trs2 = -8.9e-6)
dp..model dplcapmod = (cjo = 1.35e-9, isl =10e-30, nl =10, m = 0.53)
m..model mmedmod = (type=_n, vto = 3.7, kp = 9, is =1e-30, tox=1)
m..model mstrongmod = (type=_n, vto = 4.4, kp = 250, is = 1e-30, tox = 1)
m..model mweakmod = (type=_n, vto = 3.05, kp = 0.03, is = 1e-30, tox = 1, rs=0.1)
sw_vcsp..model s1amod = (ron = 1e-5, roff = 0.1, von = -4.0, voff = -1.5)
sw_vcsp..model s1bmod = (ron =1e-5, roff = 0.1, von = -1.5, voff = -4.0)
sw_vcsp..model s2amod = (ron = 1e-5, roff = 0.1, von = -1.0, voff = 0.5)
sw_vcsp..model s2bmod = (ron = 1e-5, roff = 0.1, von = 0.5, voff = -1.0)

c.ca n12 n8 = 1.5e-9
c.cb n15 n14 = 1.5e-9
c.cin n6 n8 = 6.4e-9

dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod

i.it n8 n17 = 1

l.ldrain n2 n5 = 1e-9
l.lgate n1 n9 = 4.81e-9
l.lsource n3 n7 = 4.63e-9

m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u

res.rbreak n17 n18 = 1, tc1 = 1.05e-3, tc2 = -9e-7
res.rdrain n50 n16 = 9e-4, tc1 = 1.9e-2, tc2 = 4e-5
res.rgate n9 n20 = 1.36
res.rldrain n2 n5 = 10
res.rlgate n1 n9 = 48.1
res.rlsource n3 n7 = 46.3
res.rslc1 n5 n51= 1e-6, tc1 = 1e-3, tc2 =1e-5
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 2.3e-3, tc1 = 1e-3, tc2 =1e-6
res.rvtemp n18 n19 = 1, tc1 = -2.4e-3, tc2 = 1e-6
res.rvthres n22 n8 = 1, tc1 = -6e-3, tc2 = -1.9e-5

spe.ebreak n11 n7 n17 n18 = 82.3
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
spe.evthres n6 n21 n19 n8 = 1

sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod

v.vbat n22 n19 = dc=1

equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/250))** 10))
}
}
```



## SPICE Thermal Model

REV 23 March 2002

FDB045AN08A0T

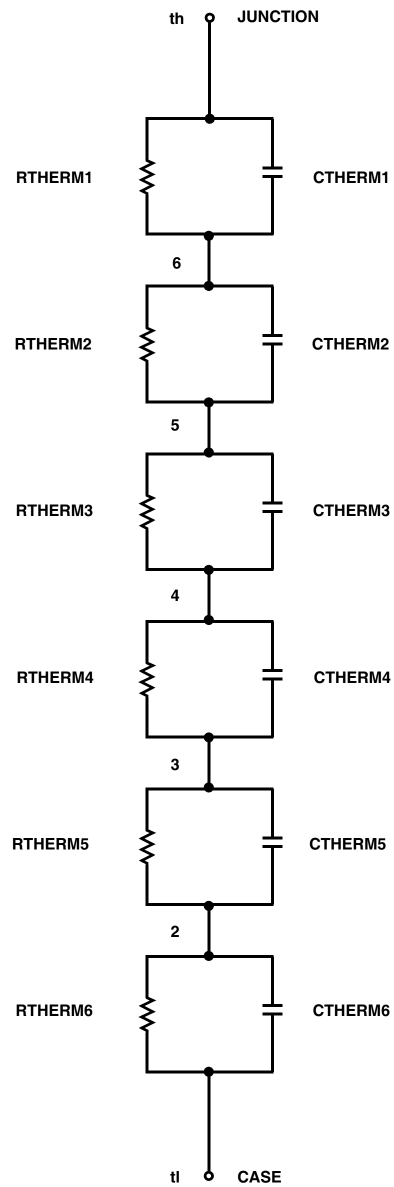
CTHERM1 th 6 6.45e-3
CTHERM2 6 5 3e-2
CTHERM3 5 4 1.4e-2
CTHERM4 4 3 1.65e-2
CTHERM5 3 2 4.85e-2
CTHERM6 2 tl 1e-1

RTHERM1 th 6 3.24e-3
RTHERM2 6 5 8.08e-3
RTHERM3 5 4 2.28e-2
RTHERM4 4 3 1e-1
RTHERM5 3 2 1.1e-1
RTHERM6 2 tl 1.4e-1

## SABER Thermal Model

SABER thermal model FDB045AN08A0T
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 6 = 6.45e-3
ctherm.ctherm2 6 5 = 3e-2
ctherm.ctherm3 5 4 = 1.4e-2
ctherm.ctherm4 4 3 = 1.65e-2
ctherm.ctherm5 3 2 = 4.85e-2
ctherm.ctherm6 2 tl = 1e-1

rtherm.rtherm1 th 6 = 3.24e-3
rtherm.rtherm2 6 5 = 8.08e-3
rtherm.rtherm3 5 4 = 2.28e-2
rtherm.rtherm4 4 3 = 1e-1
rtherm.rtherm5 3 2 = 1.1e-1
rtherm.rtherm6 2 tl = 1.4e-1
}



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